

TOSHIBA Variable Capacitance Diode Silicon Epitaxial Planar Type

1SV270

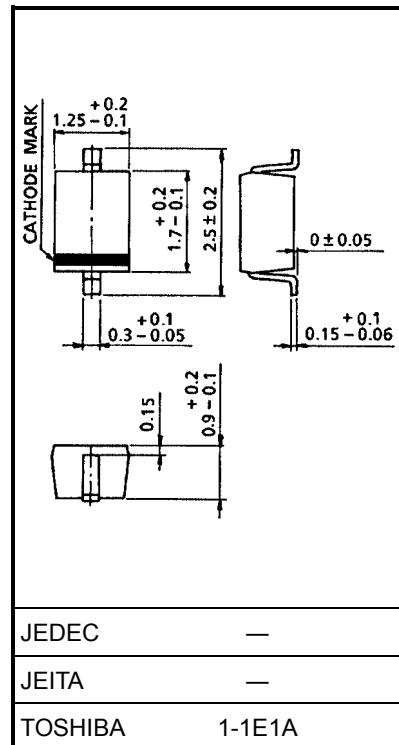
VCO for UHF Band Radio

Unit: mm

- High capacitance ratio: $C_1 V/C_4 V = 2.0$ (typ.)
- Low series resistance: $r_s = 0.28 \Omega$ (typ.)
- Small package

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C



Weight: 0.004 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1 \mu\text{A}$	10	—	—	V
Reverse current	I_R	$V_R = 10 \text{ V}$	—	—	3	nA
Capacitance	$C_1 V$	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$	15	16	17	pF
Capacitance	$C_4 V$	$V_R = 4 \text{ V}, f = 1 \text{ MHz}$	7.3	8.0	8.7	pF
Capacitance ratio	$C_1 V/C_4 V$	—	1.8	2.0	—	—
Series resistance	r_s	$V_R = 1 \text{ V}, f = 470 \text{ MHz}$	—	0.28	0.5	Ω

Marking